## Answer on Question #51241, Physics, Solid State Physics

Calculate the intrinsic carrier concentration for GaAs at 300 K, given that,

$$mh = me \ me = me \ Eg = eV$$

T = 300K

 $m_v = 0.56 m_e$ 

 $m_c = 0.068 m_a$ 

 $\Delta W = 1.42 eV$ 

## **Solution**

The own concentration of charge carriers is given by Eq.(1)

$$n_i = \sqrt{N_c N_v} \exp\left(-\frac{\Delta W}{2kT}\right) \tag{1}$$

where  $k = 1.38 \cdot 10^{-23} J/K$  is the Boltzmann constant; T = 300K is the temperature.

Effective density of states for electrons in the conduction band is given by Eq.(2).

$$N_c = \frac{2(2 \cdot \pi \cdot m_c \cdot k \cdot T)^{3/2}}{h^3} = \frac{2(2 \cdot \pi \cdot 0.56 \cdot 9, 1 \cdot 10^{-31} kg \cdot 1, 38 \cdot 10^{-23} J / K \cdot 300 K)^{3/2}}{(6,62 \cdot 10^{-34})^3} = 1.05 \cdot 10^{25} m^{-3} \quad (2)$$

where  $h = 6.62 \cdot 10^{-34} J \cdot s$  is the Planck constant.

Effective density of states for holes in the valence band is given by Eq.(3).

$$N_{v} = \frac{2(2 \cdot \pi \cdot m_{v} \cdot k \cdot T)^{3/2}}{h^{3}} = \frac{2(2 \cdot \pi \cdot 0.068 \cdot 9.1 \cdot 10^{-31} \cdot 1.38 \cdot 10^{23} T)^{3/2}}{(6.62 \cdot 10^{34})^{-3}} = 4.45 \cdot 10^{23} m^{-3}$$
(3)

The intrinsic concentration

$$n_i = 10^{23} \sqrt{1.05 \cdot 100 \cdot 4.45} \exp\left(-\frac{1.42}{2 \cdot 8.625 \cdot 10^{-5} \cdot 300}\right) \approx 2.6 \cdot 10^{12} m^{-3}$$
 (4)

**Answer:**  $n_i \approx 2.6 \cdot 10^{12} m^{-3}$ 

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